

### **Comparison of GaAs based high voltage diode stacks**

**Voitoviš, Viktor; Kuznetsova, Natalja; Rang, Toomas; Pikkov, Mihhail; Ruut, Jana** EPE-PEMC 2004 : 11th International Power Electronics and Motion Control Conference : 2-4 September 2004, Riga, Latvia : proceedings. Vol. 2 of 7, Devices, control of converters, measurements and sensors 2004 / p. 2-391 - 2-394 : ill

### **GaAs based diffusion welded high voltage diode stacks [Electronic resource]**

**Toompuu, Jana; Korolkov, Oleg; Sleptšuk, Natalja; Voitoviš, Viktor; Rang, Toomas** IEEE International Conference on Semiconductor Electronics CD-ROM Proceedings 2010 / [4] p

### **High performance GaAs power diodes**

**Voitoviš, Viktor; Rang, Toomas; Rang, Galina; Pikkov, Mihhail** BEC 2008 : 2008 International Biennial Baltic Electronics Conference : proceedings of the 11th Biennial Baltic Electronics Conference : Tallinn University of Technology : October 6-8, 2008, Tallinn, Estonia 2008 / p. 111-114 : ill

### **High voltage GaAs diode stacks : the choice of epistuctures for assembling**

**Rang, Toomas; Voitoviš, Viktor; Kuznetsova, Natalja** Design, Test, Integration and Packaging of MEMS/MOEMS - DTIP2004 : 12-14 May 2004, Montreux, Switzerland 2004 / p. 199-202 : ill

### **LPE process for industrial production of power GaAs rectifiers**

**Voitoviš, Viktor** Abstract book of 12th American Conference on Crystal Growth and Epitaxy : August 13-18, 2000, Vail, Colorado, USA 2000 / p. 114

### **LPE structures for power GaAs rectifiers**

**Voitoviš, Viktor** The 7th Biennial Conference on Electronics and Microsystem Technology "Baltic Electronics Conference" : BEC 2000 : October 8 - 11, 2000, Tallinn, Estonia : conference proceedings 2000 / p. 237-240 : ill  
[https://artiklid.elnet.ee/record=b1005558\\*est](https://artiklid.elnet.ee/record=b1005558*est)

### **Subcontact layers in LPE structures for forming the ohmic contacts on GaAs semiconductor substrates**

**Korolkov, Oleg; Voitoviš, Viktor; Rang, Toomas** Abstract book of 13th American Conference on Crystal Growth and Epitaxy : August 12-16, 2001, Burlington, Vermont, USA 2001 / p. 133